

# PJT7838

## 50V N-Channel Enhancement Mode MOSFET

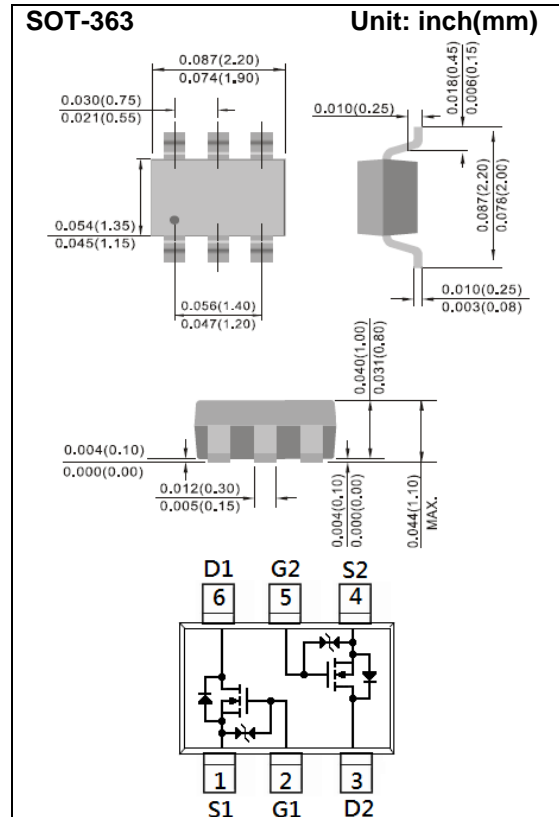
**Voltage**    **50 V**    **Current**    **400mA**

### Features

- RDS(ON) , VGS@10V, ID@500mA<1.45Ω
- RDS(ON) , VGS@4.5V, ID@200mA<1.95Ω
- RDS(ON) , VGS@2.5V, ID@100mA<4.0Ω
- RDS(ON) , VGS@1.8V, ID@10mA<6.0Ω
- Advanced Trench Process Technology
- ESD Protected 2KV HBM
- Specially Designed for Relay driver, Speed line drive, etc.
- Lead free in compliance with EU RoHS 2011/65/EU directive
- Green molding compound as per IEC61249 Std. (Halogen Free)

### Mechanical Data

- Case : SOT-363 Package
- Terminals : Solderable per MIL-STD-750, Method 2026
- Approx. Weight : 0.0002 ounces, 0.006 grams
- Marking: T38



### Maximum Ratings and Thermal Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	LIMIT	UNITS
Drain-Source Voltage	V <sub>DS</sub>	50	V
Gate-Source Voltage	V <sub>GS</sub>	±20	V
Continuous Drain Current	I <sub>D</sub>	400	mA
Pulsed Drain Current	I <sub>DM</sub>	1200	mA
Power Dissipation	P <sub>D</sub>	T <sub>A</sub> =25°C	350
		Derate above 25°C	2.8
Operating Junction and Storage Temperature Range	T <sub>J</sub> , T <sub>STG</sub>	-55~150	°C
Typical Thermal resistance	R <sub>θJA</sub>	357	°C/W
- Junction to Ambient (Note 3)			

# PJT7838

## Electrical Characteristics (T<sub>A</sub>=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS
<b>Static</b>						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>D</sub> =250uA	50	-	-	V
Gate Threshold Voltage	V <sub>GS(th)</sub>	V <sub>DS</sub> =V <sub>GS</sub> , I <sub>D</sub> =250uA	0.5	0.86	1.0	V
Drain-Source On-State Resistance	R <sub>DS(on)</sub>	V <sub>GS</sub> =10V, I <sub>D</sub> =500mA	-	1.2	1.45	Ω
		V <sub>GS</sub> =4.5V, I <sub>D</sub> =200mA	-	1.3	1.95	
		V <sub>GS</sub> =2.5V, I <sub>D</sub> =100mA	-	1.7	4.0	
		V <sub>GS</sub> =1.8V, I <sub>D</sub> =10mA	-	4.0	6.0	
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =50V, V <sub>GS</sub> =0V	-	-	1	uA
Gate-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±20V, V <sub>DS</sub> =0V	-	-	±10	uA
<b>Dynamic</b> (Note 4)						
Total Gate Charge	Q <sub>g</sub>	V <sub>DS</sub> =25V, I <sub>D</sub> =500mA, V <sub>GS</sub> =4.5V	-	0.95	-	nC
Gate-Source Charge	Q <sub>gs</sub>		-	0.34	-	
Gate-Drain Charge	Q <sub>gd</sub>		-	0.32	-	
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> =25V, V <sub>GS</sub> =0V, f=1.0MHZ	-	36	-	pF
Output Capacitance	C <sub>oss</sub>		-	11	-	
Reverse Transfer Capacitance	C <sub>rss</sub>		-	6.6	-	
Turn-On Delay Time	t <sub>d(on)</sub>	V <sub>DD</sub> =25V, I <sub>D</sub> =500mA, V <sub>GS</sub> =10V, R <sub>G</sub> =6Ω (Note 1,2)	-	2.3	-	ns
Turn-On Rise Time	t <sub>r</sub>		-	20	-	
Turn-Off Delay Time	t <sub>d(off)</sub>		-	7	-	
Turn-Off Fall Time	t <sub>f</sub>		-	20	-	
<b>Drain-Source Diode</b>						
Maximum Continuous Drain-Source Diode Forward Current	I <sub>S</sub>	---	-	-	500	mA
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> =500mA, V <sub>GS</sub> =0V	-	0.9	1.5	V

**NOTES :**

1. Pulse width ≤ 300us, Duty cycle ≤ 2%
2. Essentially independent of operating temperature typical characteristics.
3. R<sub>θJA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. mounted on a 1 inch square pad of copper
4. Guaranteed by design, not subject to production testing.

# PJT7838

## TYPICAL CHARACTERISTIC CURVES

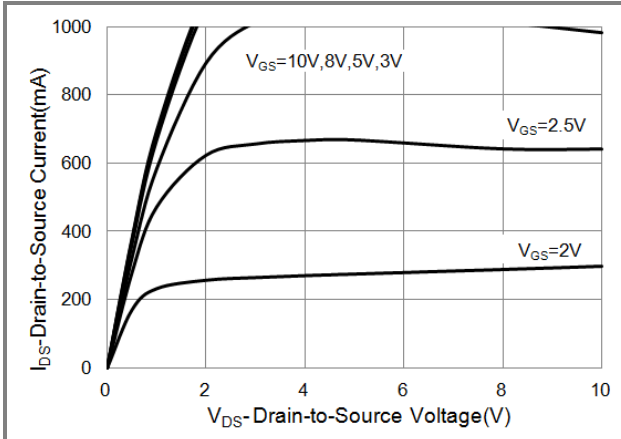


Fig.1 On-Region Characteristics

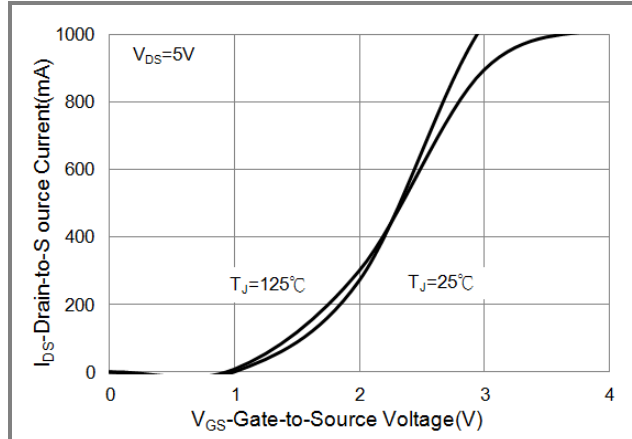


Fig.2 Transfer Characteristics

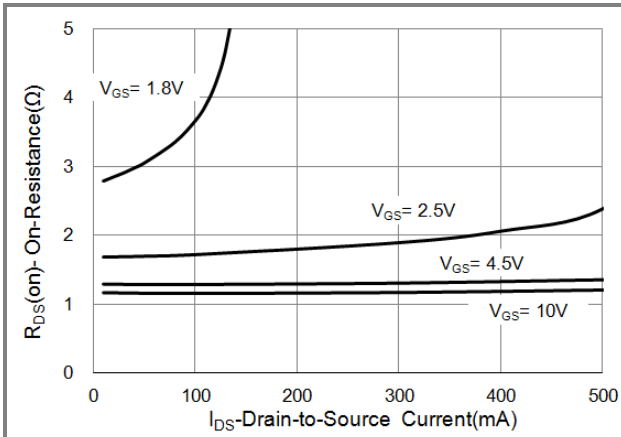


Fig.3 On-Resistance vs. Drain Current

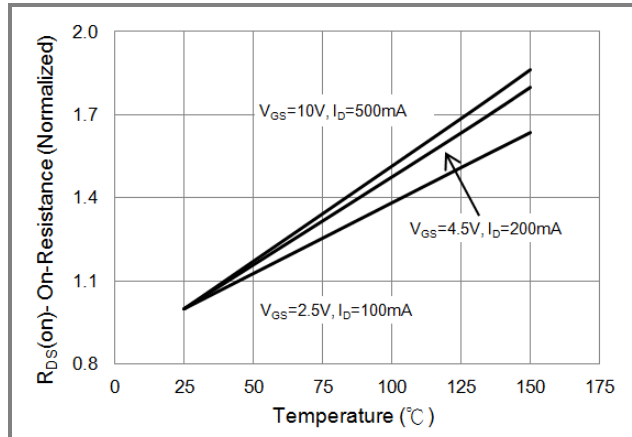


Fig.4 On-Resistance vs. Junction temperature

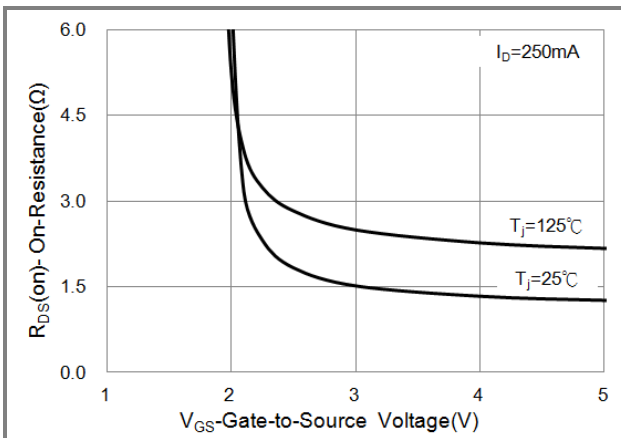


Fig.5 On-Resistance Variation with VGS.

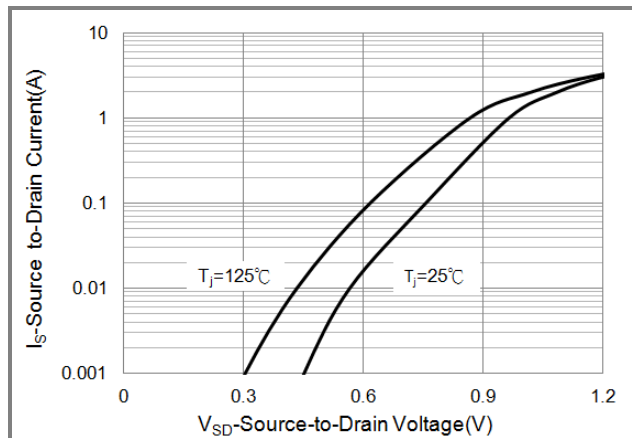


Fig.6 Body Diode Characteristics

# PJT7838

## TYPICAL CHARACTERISTIC CURVES

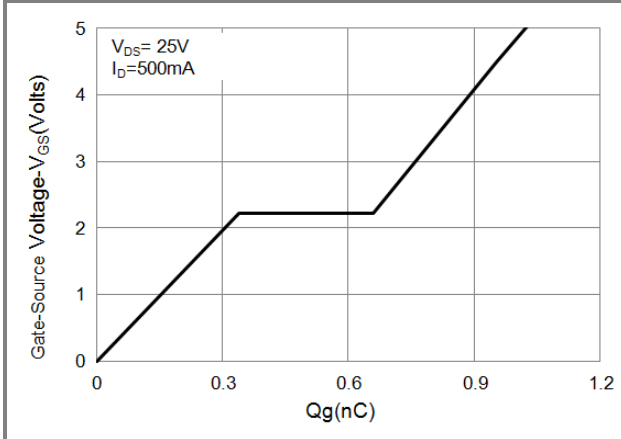


Fig.7 Gate-Charge Characteristics

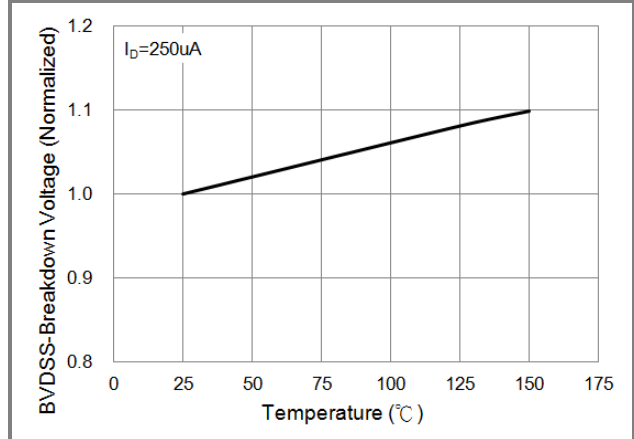


Fig.8 Breakdown Voltage Variation vs. Temperature

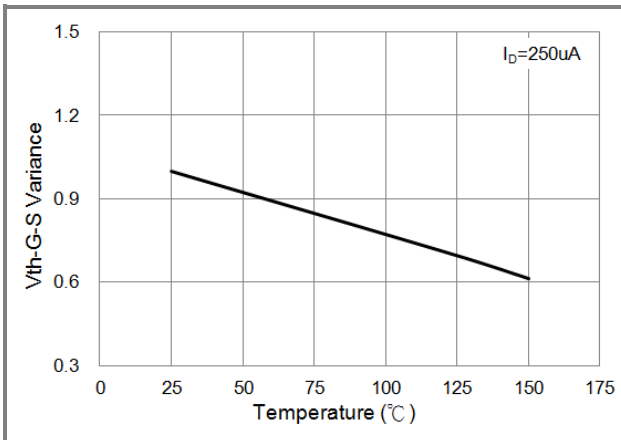


Fig.9 Threshold Voltage Variation with Temperature.

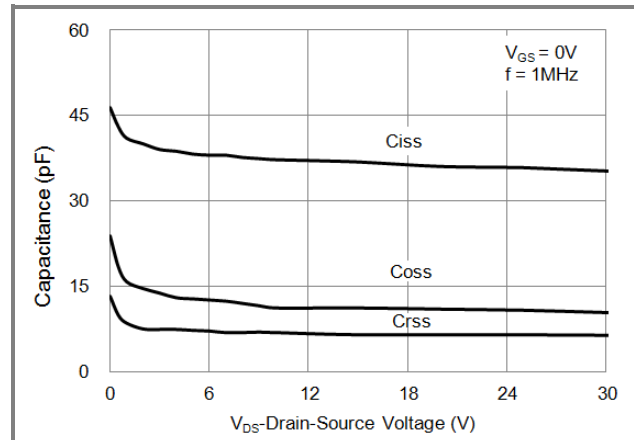


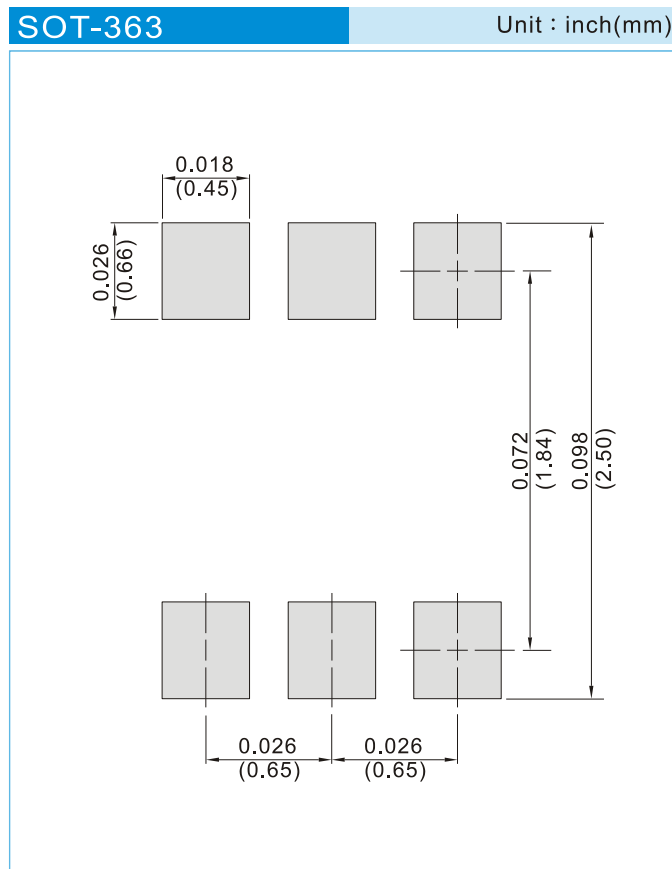
Fig.10 Capacitance vs. Drain-Source Voltage.

# PJT7838

## Product and Packing Information

Part No.	Package Type	Packing type	Marking
PJT7838	SOT-363	3K pcs / 7" reel	T38
PJT7838	SOT-363	10K pcs / 13" reel	T38

## Mounting Pad Layout



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